

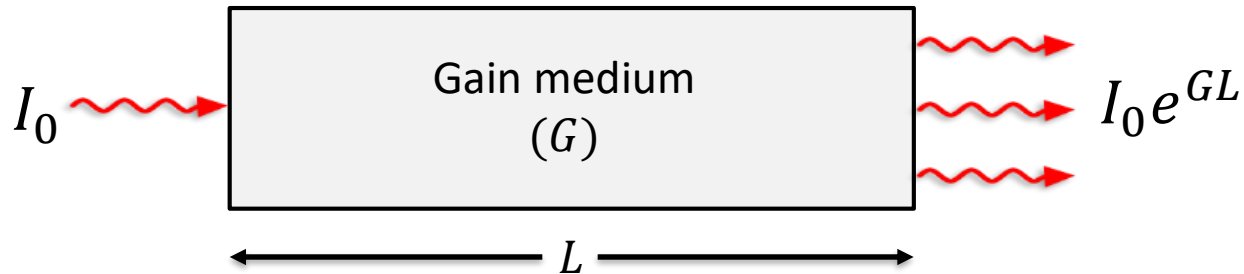
EE 232: Lightwave Devices

Lecture #2 – Optical gain and laser cavities

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Gain Medium

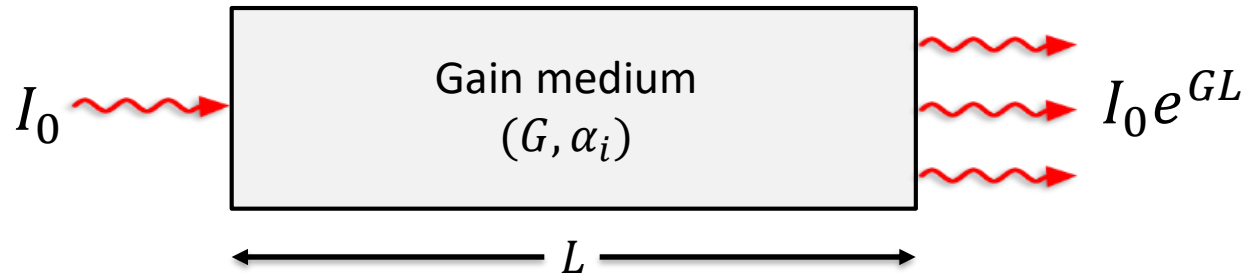


$$\begin{aligned}\Delta I &= I(z + \Delta L) - I(z) \\ &= I(z) + I(z)G\Delta L - I(z) \\ &= I(z)G\Delta L\end{aligned}$$

$$G = \frac{\Delta I}{I} \frac{1}{\Delta L}$$

Gain is the fractional increase in light intensity per unit length (Units are cm^{-1})

Gain Medium (with internal loss)



$$\Delta I = I(z + \Delta L) - I(z)$$

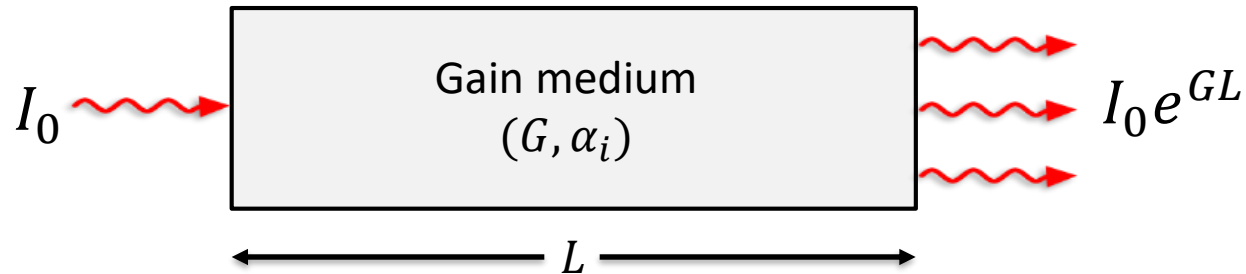
$$= I(z) + I(z)(G - \alpha_i)\Delta L - I(z)$$

$$= I(z)(G - \alpha_i)\Delta L$$

$$(G - \alpha_i) = \frac{\Delta I}{I} \frac{1}{\Delta L}$$

Internal loss (α_i) is the fractional decrease in light intensity per unit length (unrelated to fundamental absorption) (Units are cm^{-1})

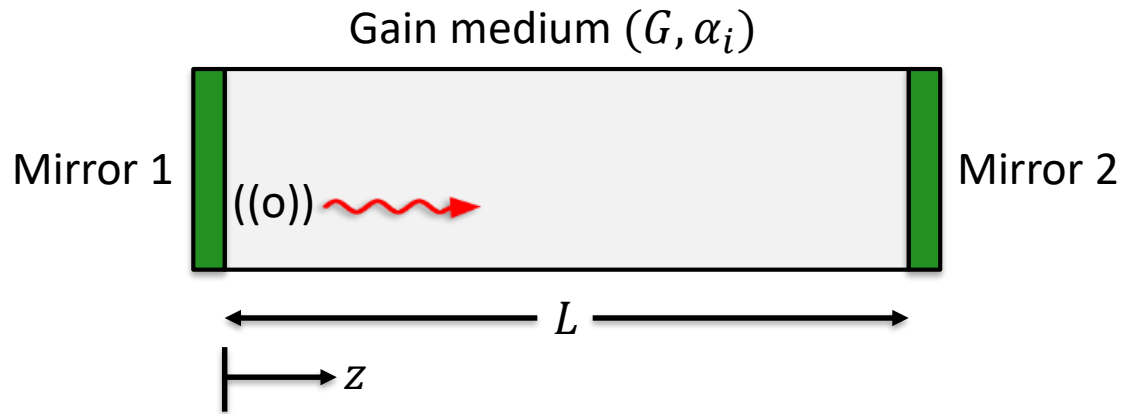
Gain Medium (with internal loss)



$$(G - \alpha_i) = \frac{\Delta I}{I} \frac{1}{\Delta L} \rightarrow \frac{dI}{dz} \frac{1}{I}$$

$$I(z) = I_0 e^{(G - \alpha_i)z}$$

Gain with cavity

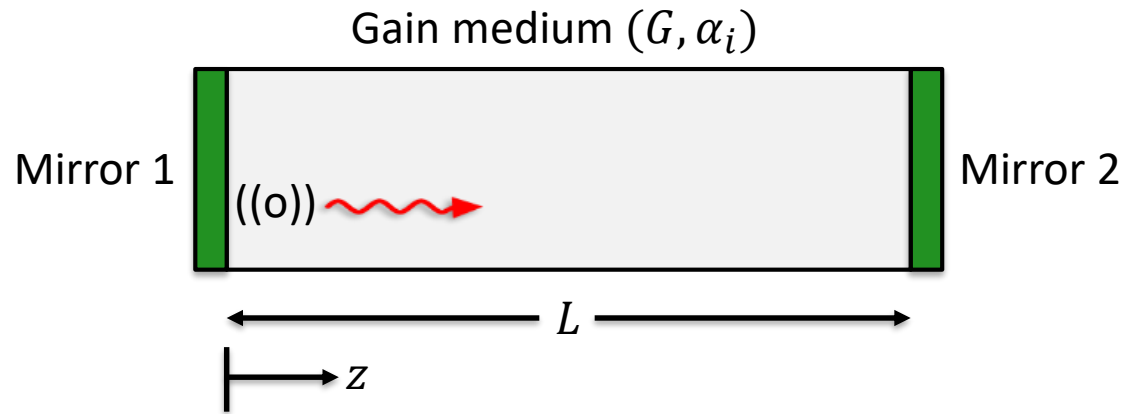


$$1 = \frac{I(z = 0^+ + 2L)}{I(z = 0^+)} = e^{2(G_{th} - \alpha_i)L} R_2 R_1$$

↑
Round-trip gain

(Threshold condition
for self-sustaining
oscillation)

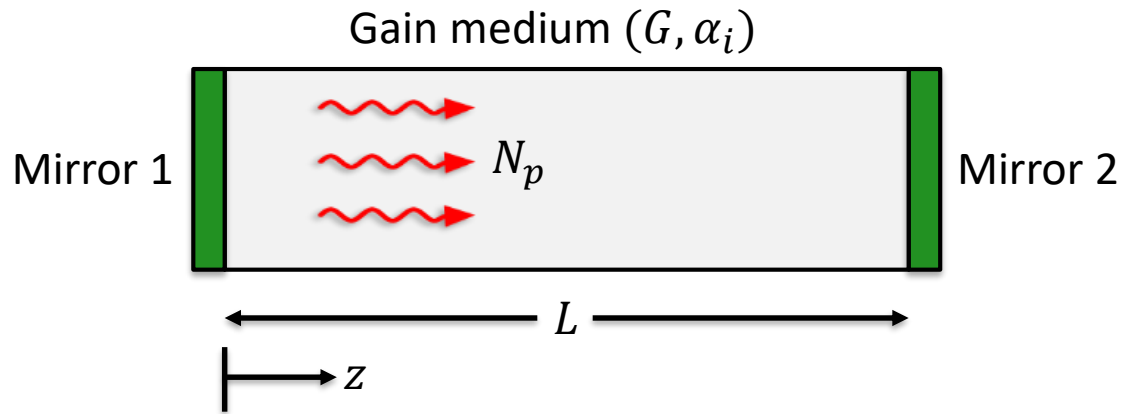
Gain with cavity



$$G_{th} = \frac{1}{2L} \ln \left(\frac{1}{R_2 R_1} \right) + \alpha_i$$
$$= \alpha_m + \alpha_i$$

(Threshold condition
for self-sustaining
oscillation)

Photon lifetime (τ_p)

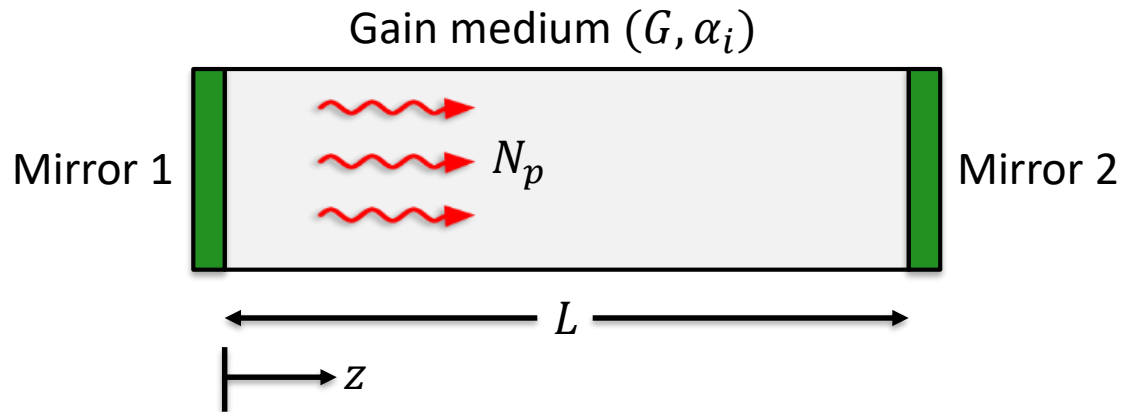


After one round trip: $(1 - R_1 R_2) N_p$ photons are lost from the cavity (ignoring α_i)

$$\frac{\Delta N_p}{\Delta t} = \frac{N_p(t + \tau_{RT}) - N_p(t)}{\tau_{RT}} = -\frac{(1 - R_1 R_2) N_p}{\tau_{RT}}$$

$$N_p = N_{p0} e^{-t/\tau_p} \quad \text{where} \quad \tau_p = \frac{2nL/c}{1 - R_1 R_2} \quad (\text{photon lifetime})$$

Quality factor (Q)

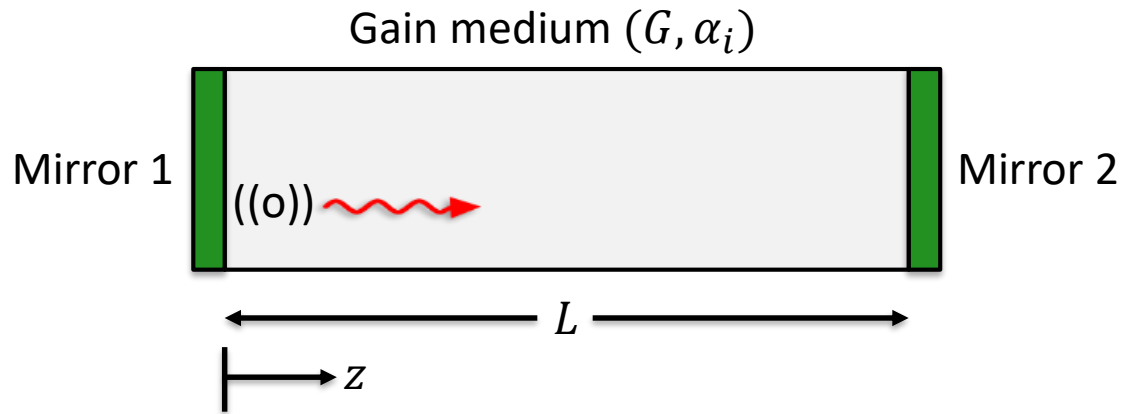


$$Q = 2\pi \frac{\text{Energy stored in cavity}}{\text{Energy lost per cycle}}$$

$$Q = 2\pi \frac{N_p \hbar \omega}{\frac{N_p \hbar \omega}{\tau_p} T} = \frac{2\pi}{T} \tau_p$$

$$Q = \omega_0 \tau_p$$

Alternative expression for G_{th}

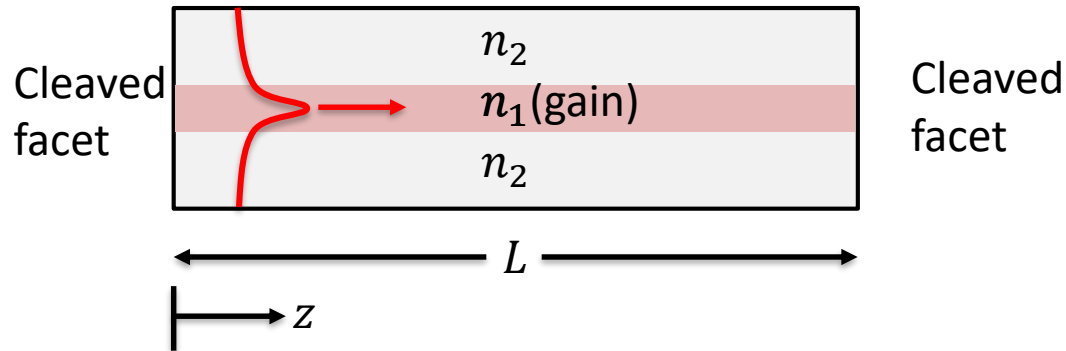


$G \frac{c}{n}$ is the fractional increase in photons per second

$$G_{th} \frac{c}{n} N_p = \frac{N_p}{\tau_p}$$

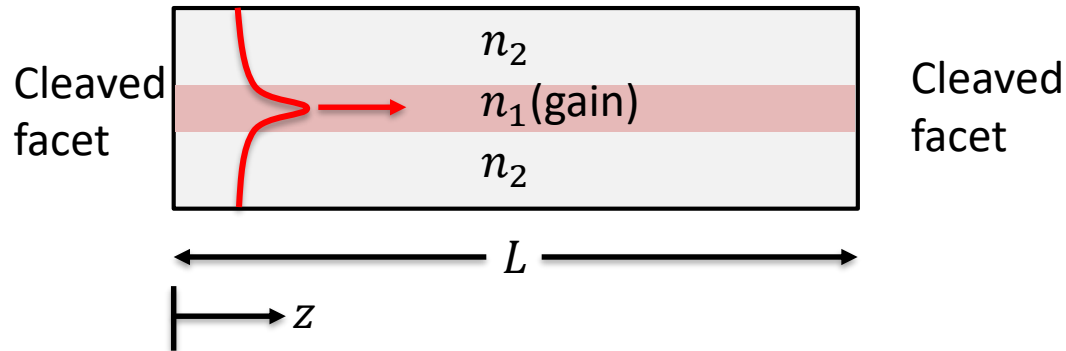
$$G_{th} \frac{c}{n} \tau_p = 1 \rightarrow G_{th} = \frac{\omega_0}{Q} \frac{n}{c}$$

Semiconductor laser



$$R = \left(\frac{n-1}{n+1} \right)^2 \sim 30\% \text{ for } n = 3.5$$

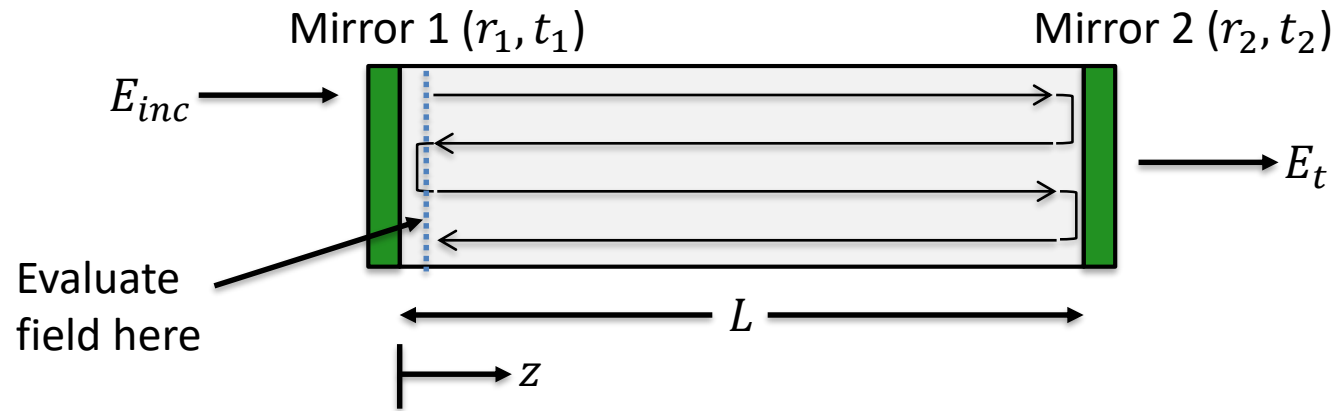
Semiconductor laser



Confinement factor: $\Gamma = \frac{\text{Power of optical mode in gain region}}{\text{Total power of optical mode}}$

$$G_{th} = \frac{1}{\Gamma} \frac{\omega_0}{Q} \frac{n}{c}$$

Fabry-Perot cavity modes



Field just to the right of Mirror 1 and propagating in +z direction:

$$E^+ = E_{inc} t_1 (1 + r_1 r_2 e^{-jk2L} + r_1 r_2 r_1 r_2 e^{-jk4L} + (r_1 r_2 e^{-jk2L})^3 + \dots)$$

$$\sum_k^{\infty} ar^k = \frac{a}{1-r}$$

$$E^+ = E_{inc} t_1 \frac{1}{1 - r_1 r_2 e^{-j2\theta}} \quad \text{where } \theta = kL$$

E^+ is the field traveling to the right (+z direction)

Fabry-Perot cavity modes

$$\text{Transmission } T = \frac{I_t}{I_{inc}} = \frac{\langle S_t \rangle}{\langle S_{inc} \rangle} = \frac{\frac{|E^+|^2 t_2^2}{2\eta_0}}{\frac{|E_{inc}|^2}{2\eta_0}}$$

Assume that $r_{1,2}$ and $t_{1,2}$ are real for simplicity

$$\begin{aligned} &= \frac{\left| E_{inc} t_1 \frac{1}{1 - r_1 r_2 e^{-j2\theta}} \right|^2 t_2^2}{|E_{inc}|^2} \\ &= \frac{t_1^2 t_2^2}{|1 - r_1 r_2 e^{-j2\theta}|^2} \\ &= \frac{(1 - r_1^2) \eta_{cavity} \eta_0^{-1} (1 - r_2^2) \eta_0 \eta_{cavity}^{-1}}{|1 - r_1 r_2 e^{-j2\theta}|^2} \\ &= \frac{(1 - r_1^2)(1 - r_2^2)}{|1 - r_1 r_2 e^{-j2\theta}|^2} \end{aligned}$$

$\langle S \rangle$: Time-average Poynting vector (intensity)

η_0 : Impedance of medium outside cavity

η_{cavity} : Impedance of medium inside cavity

t_1 : transmission of mirror 1

r_1 : reflectivity of mirror 1

t_2 : transmission of mirror 2

r_2 : reflectivity of mirror 2

$$t_1^2 \eta_0 \eta_{cavity}^{-1} + r_1^2 = 1$$

$$t_2^2 \eta_0^{-1} \eta_{cavity} + r_2^2 = 1$$

Fabry-Perot cavity modes

$$\begin{aligned}
 &= \frac{(1-r_1^2)(1-r_2^2)}{|1-r_1r_2e^{-j2\theta}|^2} \\
 &= \frac{(1-r_1^2)(1-r_2^2)}{(1-r_1r_2e^{j2\theta})(1-r_1r_2e^{-j2\theta})} \\
 &= \frac{(1-r_1^2)(1-r_2^2)}{1-r_1r_2[e^{j2\theta} + e^{-j2\theta}] + (r_1r_2)^2} \\
 &= \frac{(1-r_1^2)(1-r_2^2)}{1-2r_1r_2[\cos 2\theta] + (r_1r_2)^2} \\
 &= \frac{(1-r_1^2)(1-r_2^2)}{1-2r_1r_2[1-2\sin^2 \theta] + (r_1r_2)^2} \\
 &= \frac{(1-r_1^2)(1-r_2^2)}{1-2r_1r_2 + 4r_1r_2 \sin^2 \theta + (r_1r_2)^2}
 \end{aligned}$$

$$T = \frac{(1-r_1^2)(1-r_2^2)}{(1-r_1r_2)^2 + 4r_1r_2 \sin^2 kL}$$

$\langle S \rangle$: Time-average Poynting vector (intensity)

η_0 : Impedance of medium outside cavity

η_{cavity} : Impedance of medium inside cavity

t_1 : transmission of mirror 1

r_1 : reflectivity of mirror 1

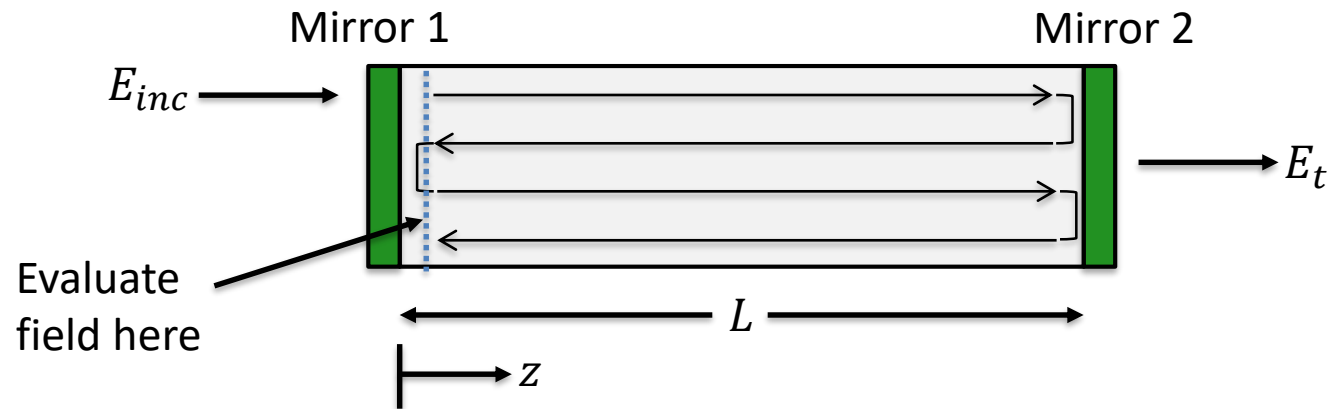
t_2 : transmission of mirror 2

r_2 : reflectivity of mirror 2

$$t_1^2 \eta_0 \eta_{cavity}^{-1} + r_1^2 = 1$$

$$t_2^2 \eta_0^{-1} \eta_{cavity} + r_2^2 = 1$$

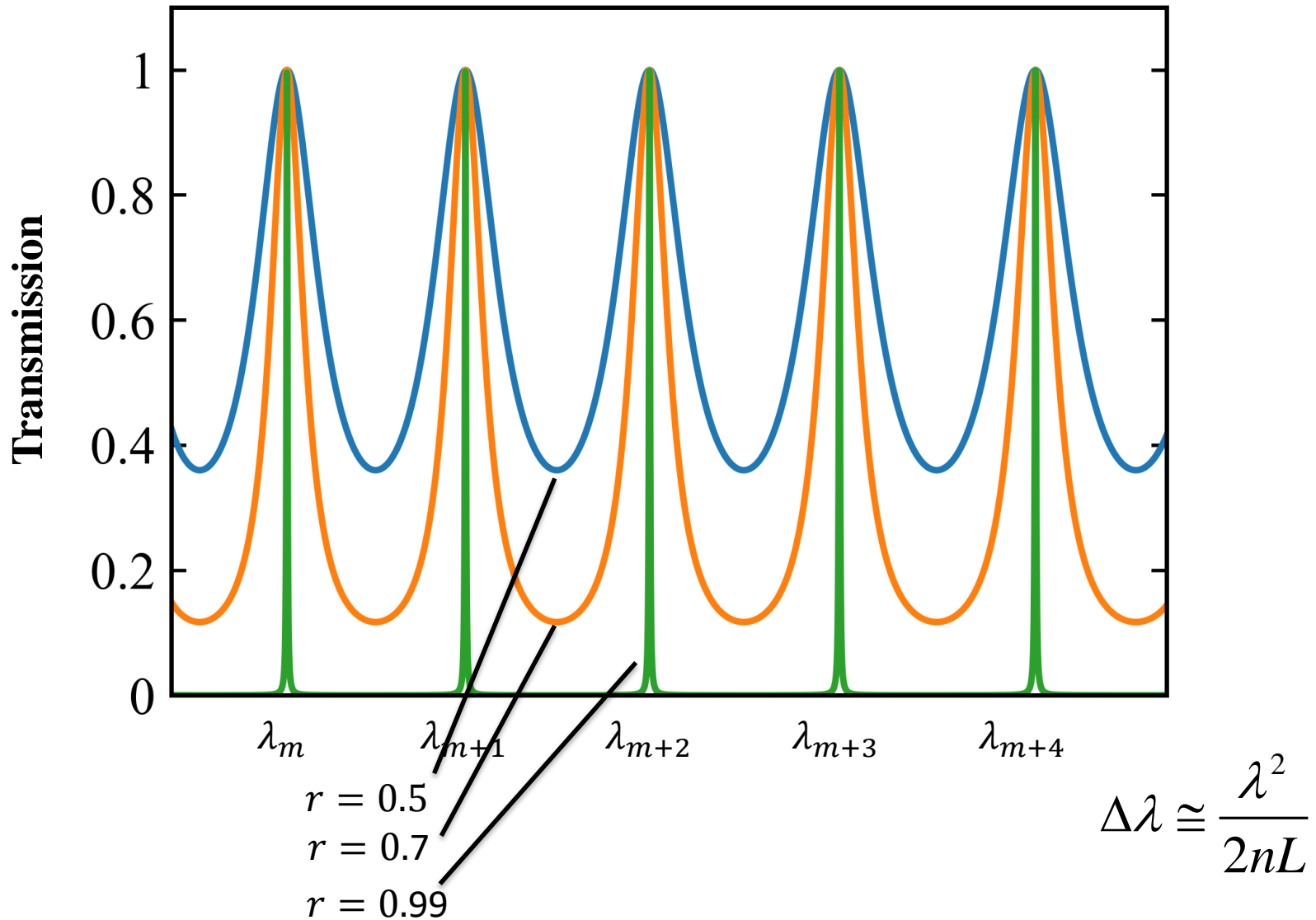
Fabry-Perot cavity modes



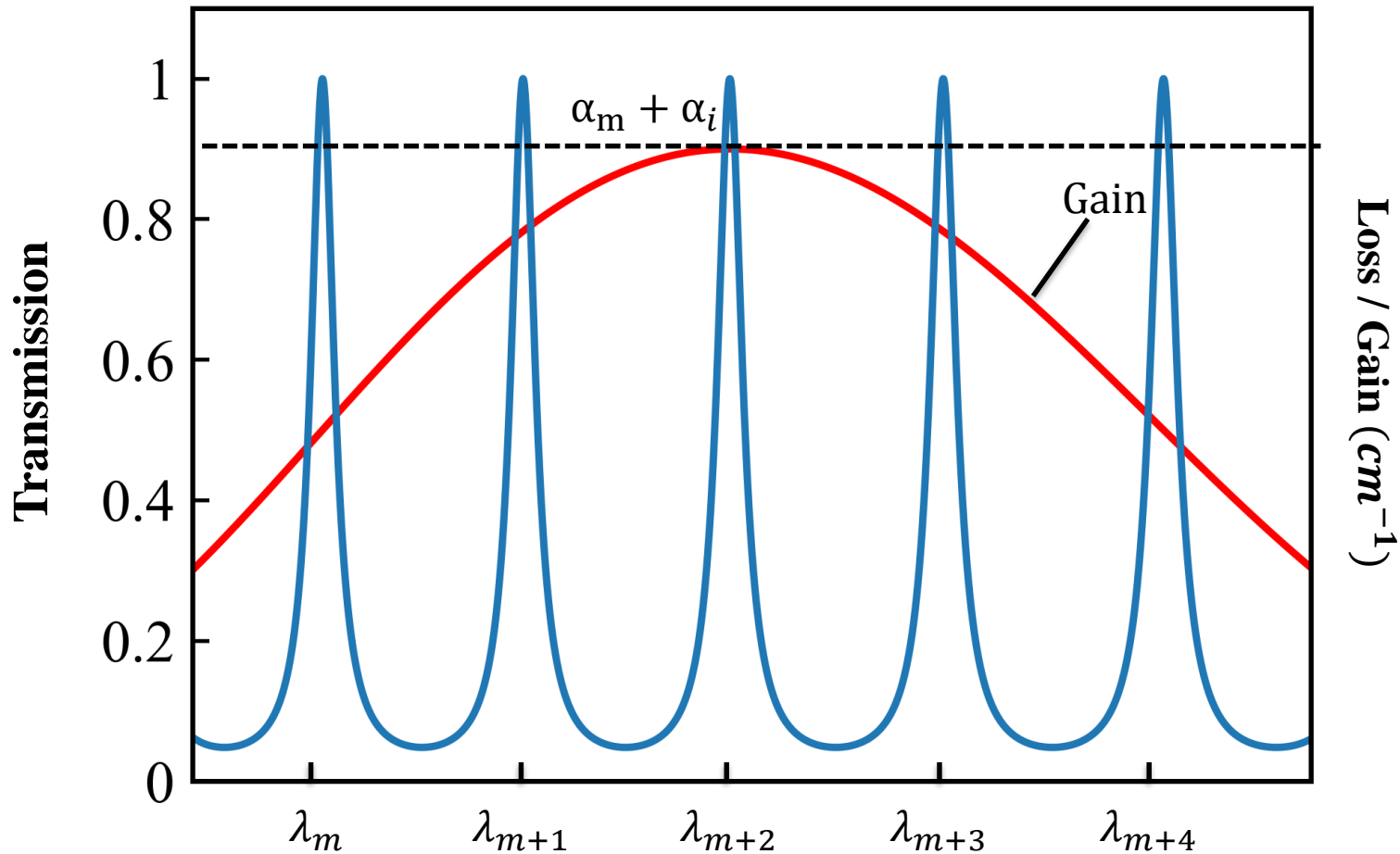
Resonance condition: $\sin^2 \theta = 0 \rightarrow kL = m\pi$

$$L = \frac{m\lambda_0}{2n} \quad m = \text{integer}$$

Fabry-Perot cavity modes



Fabry-Perot cavity modes

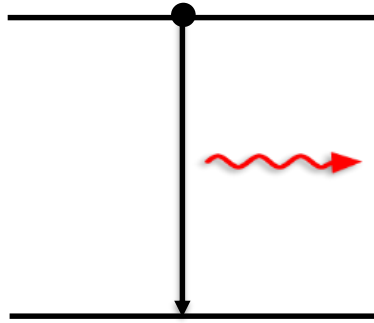


e.g. with simple gain curve

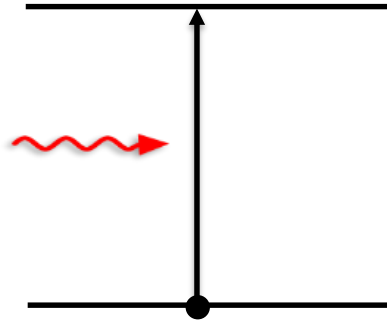
Threshold is achieved for one Fabry-Perot mode.

Population inversion

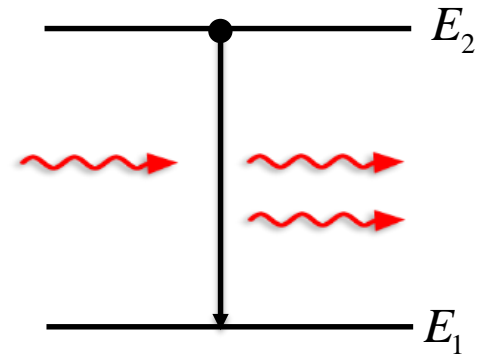
Spontaneous emission



Absorption



Stimulated emission



Gain will occur if stimulated emission > absorption
which implies that number of electrons in the
excited state is higher than the ground state
(i.e. population inversion)

$$B_{21}WN_2 > B_{12}WN_1$$

$$N_2 > N_1$$

A_{21} = Spontaneous emission rate

$B_{21}W$ = Stimulated emission / absorption rate

W = Electromagnetic energy density

N_1 = Number of electrons in ground state

N_2 = Number of electrons in excited state

N_p = Number of photons

2-level system

$$\frac{dN_1}{dt} = -A_{21}N_2 + B_{21}WN_1 - B_{21}WN_2$$

At equilibrium,

$$0 = -A_{21}N_2 + B_{21}WN_1 - B_{21}WN_2$$

$$\text{Let } N = N_1 + N_2$$

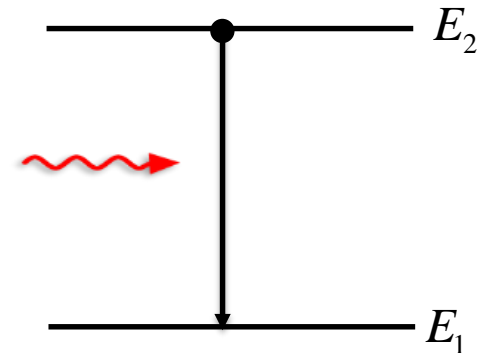
$$N_1 = \frac{A_{21} + B_{21}W}{A_{21} + 2B_{21}W} N$$

$$N_2 = \frac{B_{21}W}{A_{21} + 2B_{21}W} N$$

For population inversion $N_2 > N_1$

$$\frac{B_{21}W}{A_{21} + 2B_{21}W} N > \frac{A_{21} + B_{21}W}{A_{21} + 2B_{21}W} N$$

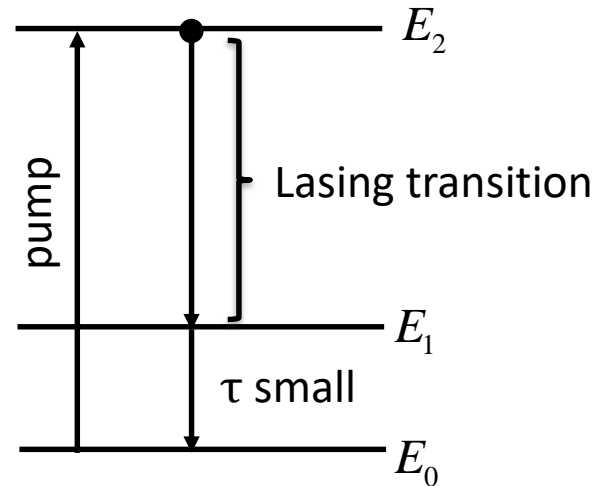
$$B_{21}W > A_{21} + B_{21}W \quad \longleftarrow$$



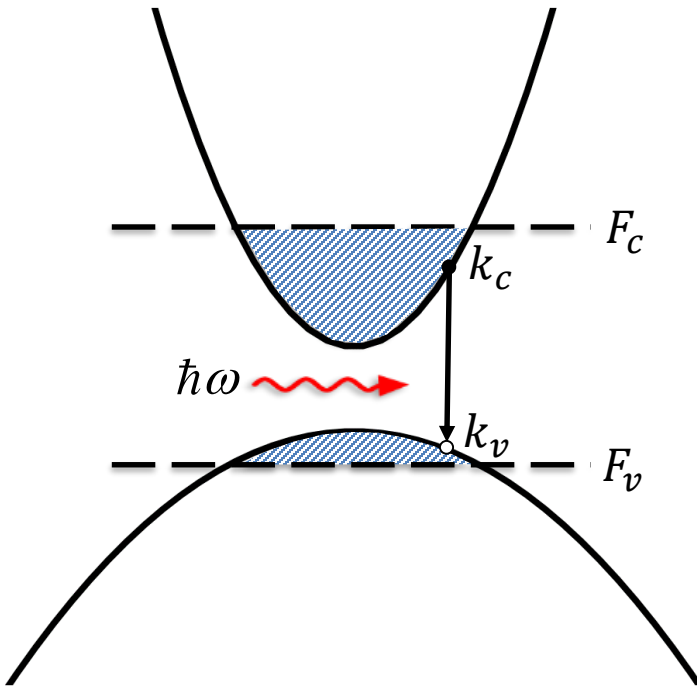
Not physical,
population inversion not possible
in a 2-level system (at equilibrium)!

3-level system

Population inversion ($N_2 > N_1$) is possible if a state with energy smaller than E_1 is added; provided electrons quickly decay from state 1 into state 0. In other words, A_{10} must be larger than A_{21} .



Gain in a semiconductor



B = transition rate coefficient
 ρ = density of states

$$f_c(k_c) = \frac{1}{1 + \exp[(E(k_c) - F_c) / kT]}$$

$$f_v(k_v) = \frac{1}{1 + \exp[(E(k_v) - F_v) / kT]}$$

$$\frac{dN_p}{dt} = B\rho f_c(1 - f_v)N_p - B\rho f_v(1 - f_c)N_p$$

↑ Stimulated emission ↑ Absorption

$$\frac{dN_p}{dt} > 0 \text{ for } f_c(1 - f_v) > f_v(1 - f_c)$$

$$\boxed{F_c - F_v > \hbar\omega} \quad \text{Bernard-Duraffourg Condition}$$

More on this as we progress in the course